

Enabling the Best Im/W in Mid Power Range

**Mid-Power LED - 5630 Series** S1W0-5630XX8003-00000000-00002 (Cool, Neutral, Warm)







### **Product Brief**

### **Description**

- This White Colored surface-mount LED comes in standard package dimension.
   Package Size: 5.6x3.0x0.65mm
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

### **Features and Benefits**

- Market Standard 5630 Package Size
- High Color Quality, CRI Min. 80
- ANSI & MacAdam 3 Step compliant
- RoHS compliant

### **Key Applications**

- Interior lighting
- General lighting
- · Indoor and outdoor displays
- Architectural / Decorative lighting

**Table 1. Product Selection Table** 

Deference Code	Reference Code Color		Darf Normhan	CRI
Reference Code Color		ССТ	Part Number	Min
		6500K	S1W0-5630658003-00000000-00002	
	Cool White	5700K	S1W0-5630578003-00000000-00002	
		5000K	\$1W0-5630508003-00000000-00002	
STW8Q14D	Neutral White	4000K	S1W0-5630408003-00000000-00002	80
		3500K	S1W0-5630358003-00000000-00002	
Warm White	Warm White	3000K	S1W0-5630308003-00000000-00002	
		2700K	S1W0-5630278003-00000000-00002	



# **Table of Contents**

Inde	ex	
•	Product Brief	1
•	Table of Contents	2
•	Performance Characteristics	3
•	Characteristics Graph	5
•	Color Bin Structure	12
•	Mechanical Dimensions	15
•	Recommended Solder Pad	16
•	Reflow Soldering Characteristics	17
•	Emitter Tape & Reel Packaging	18
•	Product Nomenclature	20
•	Handling of Silicone Resin for LEDs	21
•	Precaution For Use	22
•	Company Information	25

### **Performance Characteristics**

Table 2. Electro Optical Characteristics, I<sub>F</sub> =65mA, T<sub>i</sub>=25°C, RH30%

Min. CRI, R <sub>a</sub> <sup>(4)</sup>	Nominal CCT [K] <sup>[1]</sup>	Min. Flux [lm] @65mA	Typ. Luminous Flux Φ <sub>v</sub> <sup>[3]</sup> [lm] @65mA	Typ. Luminous Efficacy [lm/W] @65mA	Part Number
	6500	31.9	32.5	178.6	S1W0-5630658003- 00000000-00002
	5700	31.9	33.3	183.0	S1W0-5630578003- 00000000-00002
	5000	31.9	33.8	185.7	S1W0-5630508003- 00000000-00002
80	4000	31.5	33.7	185.2	S1W0-5630408003- 00000000-00002
	3500	31.2	32.5	178.6	S1W0-5630358003- 00000000-00002
	3000	31.2	32.2	176.9	S1W0-5630308003- 00000000-00002
	2700	29.7	31.4	172.5	S1W0-5630278003- 00000000-00002

#### Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of  $\pm 7\%$  on Intensity and power measurements. The luminous intensity IV was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.

Rev0.1, Dec, 2017 3 www.seoulsemicon.com



### **Performance Characteristics**

Table 3. Characteristics, I<sub>F</sub>=65mA, T<sub>i</sub>= 25°C, RH30%

Parameter	Symbol	Value			Unit
rarameter	Symbol	Min.	Тур.	Max.	Onit
Forward Current	I <sub>F</sub>	-	65	-	mA
Forward Voltage	$V_{F}$	-	2.9	3.0	V
CRI [3]	R <sub>a</sub>	80	-	-	
Viewing Angle	2Θ <sub>1/2</sub>	-	120	-	Deg.
Thermal resistance (J to S) [4]	$R\theta_{J-S}$	-	18	-	°C/W
ESD Sensitivity(HBM)	-		Class 3A JEDE0	C JS-001-2017	

**Table 4. Absolute Maximum Ratings** 

Parameter	Symbol	Value	Unit
Forward Current	l <sub>F</sub>	200	mA
Power Dissipation	$P_{D}$	0.64	W
Junction Temperature	T <sub>j</sub>	125	°C
Operating Temperature	$T_{opr}$	-40 ~ + 85	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ + 100	°C

### Notes:

- (1) Seoul Semiconductor maintains a tolerance of  $\pm 7\%$  on Intensity and power measurements.
- (2) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.

Color coordinate: ±0.005, CCT ±5% tolerance.

- (3) Tolerance is  $\pm 2.0$  on CRI measurements.
- (4) Thermal resistance is junction to Solder.
- (5) I<sub>FP</sub> conditions with pulse width ≤10ms and duty cycle ≤10%
- · Calculated performance values are for reference only.
- All measurements were made under the standardized environment of Seoul Semiconductor.

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Fig 1. Color Spectrum, T<sub>i</sub> = 25°C, I<sub>F</sub>=65mA

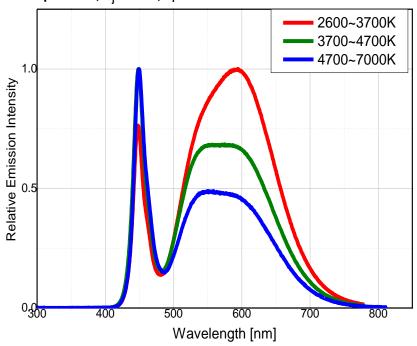


Fig 2. Radiant Pattern, T<sub>i</sub> = 25°C, I<sub>F</sub>=65mA

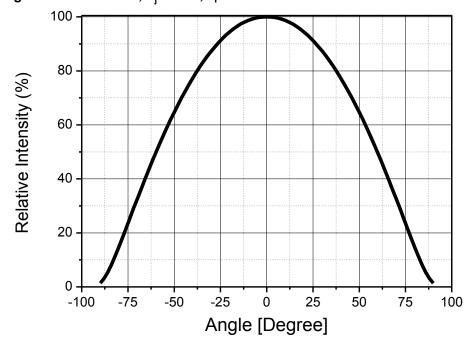


Fig 3. Forward Voltage vs. Forward Current,  $T_j = 25^{\circ}C$ 

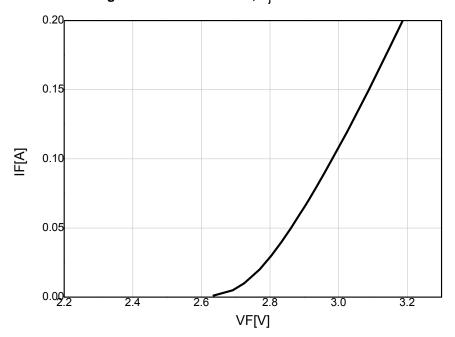


Fig 4. Forward Current vs. Relative Luminous Intensity, T<sub>i</sub> = 25°C

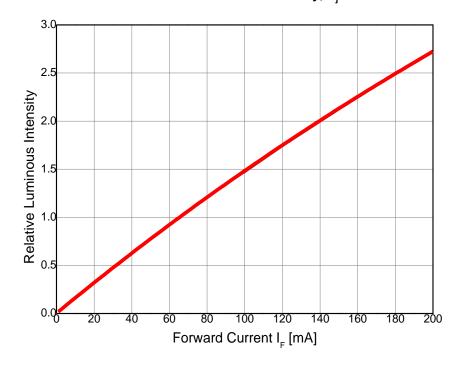
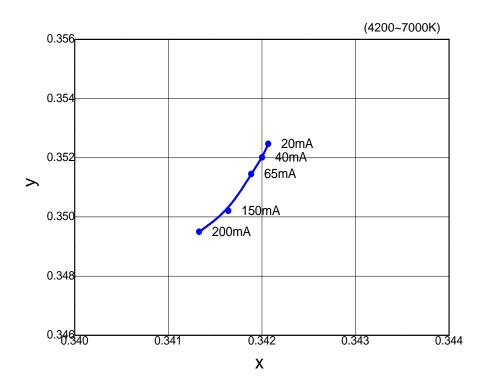


Fig 5. Forward Current vs. CIE X,Y Shift, T<sub>i</sub> = 25°C



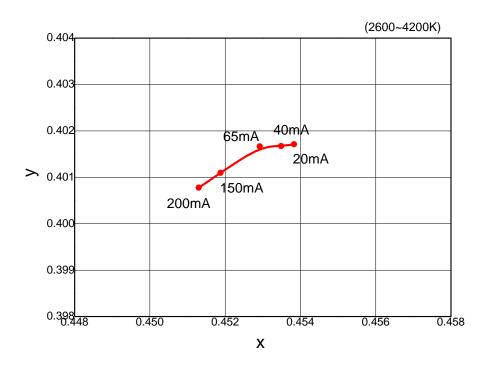


Fig 6. Junction Temperature vs. Relative Luminous Intensity, I<sub>F</sub>=65mA

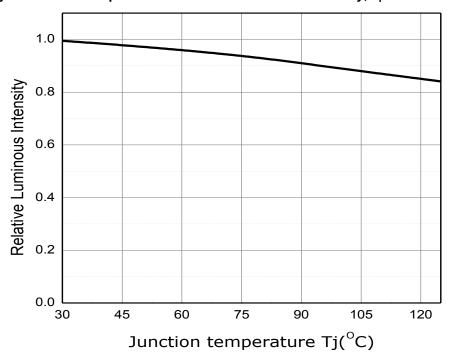


Fig 7. Junction Temperature vs. Relative Forward Voltage, I<sub>F</sub>=65mA

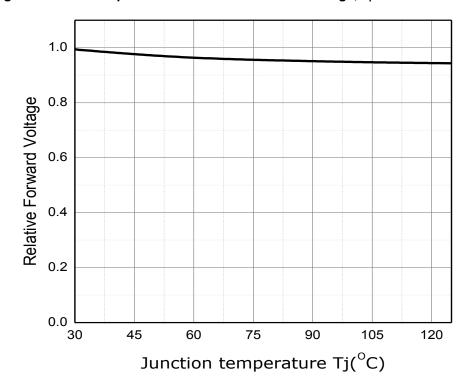
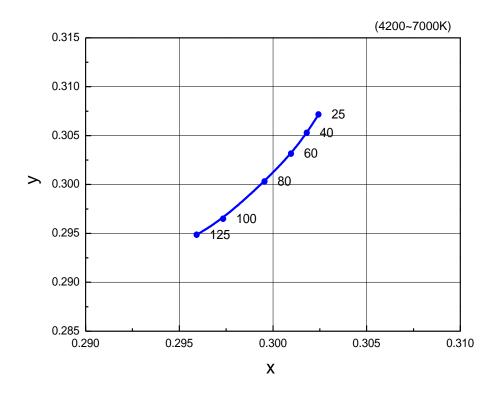


Fig 8. Chromaticity Coordinate vs. Junction Temperature, I<sub>F</sub>=65mA



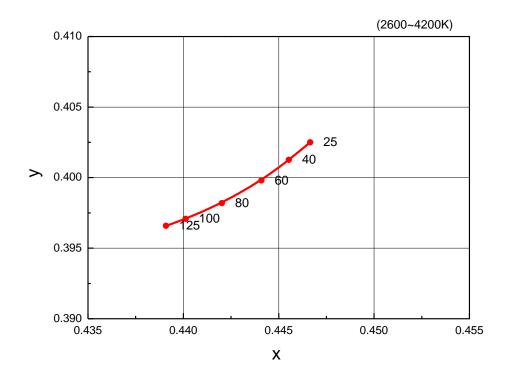
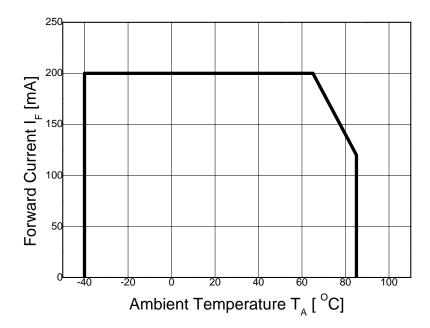


Fig 9. Ambient Temperature vs. Maximum Forward Current,  $T_{i,max} = 125^{\circ}C$ 





## **Performance Characteristics**

Table 5. Bin Code description, T<sub>i</sub>=25°C, I<sub>F</sub>=65mA

Part Number	Luminous Flux		Color	Туріса	al Forward V (V)	oltage	
Part Number	Bin Code	Min.	Max.	Chromaticity Coordinate	Bin Code	Min.	Max.
	S5	30.3	31.9	Refer to Page. 12~14	Y1	2.7	2.8
\$1W0- 5630XXXX03-	T0	31.9	33.5		Y2	2.8	2.9
00000000- 00002	T5	33.5	35.0		Y3	2.9	3.0
33302	U0	35.0	36.0				

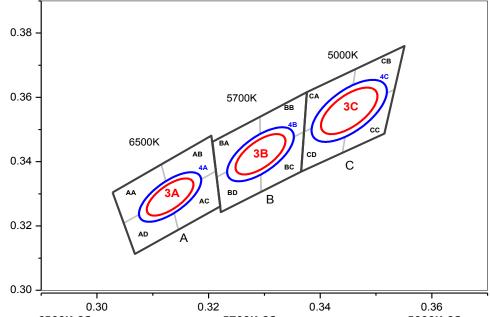
### Table 6. Intensity rank distribution

Available ranks

ССТ	CIE	IV Rank			
6000 ~ 7000K	Α	<b>S</b> 5	ТО	T5	U0
5300 – 6000K	В	S5	ТО	T5	U0
4700 ~ 5300K	С	S5	ТО	T5	U0
3700 ~ 4200K	E	S5	ТО	T5	U0
3200 ~ 3700K	F	<b>S</b> 5	TO	T5	U0
2900 ~ 3200K	G	<b>S</b> 5	T0	T5	U0
2600 ~ 2900K	Н	<b>S</b> 5	ТО	T5	U0

# **Color Bin Structure**

# CIE Chromaticity Diagram (Cool white), $T_j$ =25°C, $I_F$ =65mA



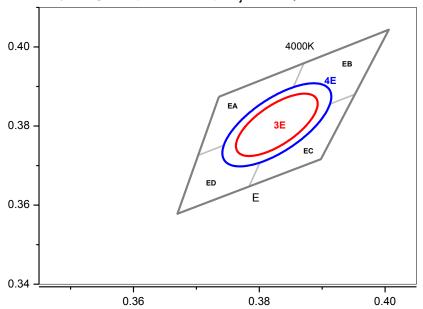
6500K 3Step		5700	K 3Step	5000K 3Step		
3A			3B	3C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0066	Major Axis a	0.0071	Major Axis a	0.0081	
Minor Axis b	0.0027	Minor Axis b	0.0030	Minor Axis b	0.0035	
Ellipse	58	Ellipse	59	Ellipse	60	
Rotation Angle	30	Rotation Angle		Rotation Angle	00	

6500K 4Step		5700	K 4Step	5000K 4Step		
	4A		4B		4C	
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0088	Major Axis a	0.0095	Major Axis a	0.0108	
Minor Axis b	0.0036	Minor Axis b	0.0040	Minor Axis b	0.0047	
Ellipse	58	Ellipse	59	Ellipse	60	
Rotation Angle	50	Rotation Angle	39	Rotation Angle	00	

Α	A	А	В	Α	С	А	D
CIE X	CIE Y						
0.3028	0.3304	0.3115	0.3393	0.3131	0.329	0.3048	0.3209
0.3048	0.3209	0.3131	0.329	0.3146	0.3187	0.3068	0.3113
0.3131	0.329	0.3213	0.3371	0.3221	0.3261	0.3146	0.3187
0.3115	0.3393	0.3205	0.3481	0.3213	0.3371	0.3131	0.329
В	A	В	В	В	C	В	D
CIE X	CIE Y						
0.3207	0.3462	0.3292	0.3539	0.3293	0.3423	0.3215	0.3353
0.3215	0.3353	0.3293	0.3423	0.3294	0.3306	0.3222	0.3243
0.3293	0.3423	0.3371	0.3493	0.3366	0.3369	0.3294	0.3306
0.3292	0.3539	0.3376	0.3616	0.3371	0.3493	0.3293	0.3423
С	A	c	В	C	C	С	D
CIE X	CIE Y						
0.3376	0.3616	0.3463	0.3687	0.3452	0.3558	0.3371	0.3493
0.3371	0.3493	0.3452	0.3558	0.344	0.3428	0.3366	0.3369
0.3452	0.3558	0.3533	0.3624	0.3514	0.3487	0.344	0.3428
0.3463	0.3687	0.3551	0.376	0.3533	0.3624	0.3452	0.3558

# **Color Bin Structure**

# CIE Chromaticity Diagram (Cool white), $T_j$ =25°C, $I_F$ =65mA



### 4000K 3Step

	3E		
Center point	0.3818 : 0.3797		
Major Axis a	0.0094		
Minor Axis b	0.0040		
Ellipse	F2		
Rotation Angle	53		

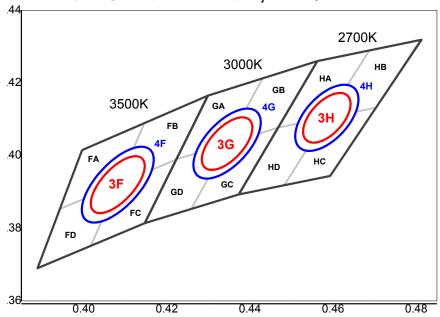
### 4000K 4Step

	4E
Center point	0.3818 : 0.3797
Major Axis a	0.0125
Minor Axis b	0.0053
Ellipse	53
Rotation Angle	53

E	A	E	В	E	с	E	D
CIE X	CIE Y						
0.3736	0.3874	0.3871	0.3959	0.3828	0.3803	0.3703	0.3726
0.3703	0.3726	0.3828	0.3803	0.3784	0.3647	0.367	0.3578
0.3828	0.3803	0.3952	0.388	0.3898	0.3716	0.3784	0.3647
0.3871	0.3959	0.4006	0.4044	0.3952	0.388	0.3828	0.3803

# **Color Bin Structure**

# CIE Chromaticity Diagram (Warm white), $T_j=25$ °C, $I_F=65$ mA

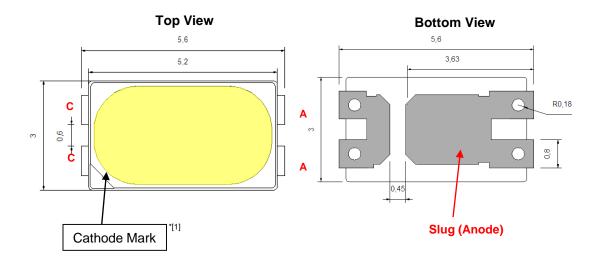


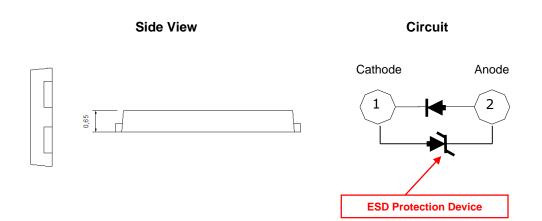
3500K 3Step		3000K 3Step		2700K 3Step	
3 Step		3 Step		3 Step	
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101
Major Axis a	0.0093	Major Axis a	0.0085	Major Axis a	0.0079
Minor Axis b	0.0041	Minor Axis b	0.0041	Minor Axis b	0.0041
Ellipse	53	Ellipse	53	Ellipse	 54
Rotation Angle	55	Rotation Angle	55	Rotation Angle	J <del>4</del>

	K 4Step		K 4Step	2700K 4Step		
4 Step		4 Step		4 Step		
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0124	Major Axis a	0.0113	Major Axis a	0.0105	
Minor Axis b	0.0055	Minor Axis b	0.0055	Minor Axis b	0.0055	
Ellipse	53	Ellipse	53	Ellipse	54	

	FA	F	В	F	C	F	D
CIE X	CIE Y						
0.3996	0.4015	0.4146	0.4089	0.4082	0.392	0.3943	0.3853
0.3943	0.3853	0.4082	0.392	0.4017	0.3751	0.3889	0.369
0.4082	0.392	0.4223	0.399	0.4147	0.3814	0.4017	0.3751
0.4146	0.4089	0.4299	0.4165	0.4223	0.399	0.4082	0.392
	GA	G	В	G	c	G	D
CIE X	CIE Y						
0.4299	0.4165	0.443	0.4212	0.4345	0.4033	0.4223	0.399
0.4223	0.399	0.4345	0.4033	0.4259	0.3853	0.4147	0.3814
0.4345	0.4033	0.4468	0.4077	0.4373	0.3893	0.4259	0.3853
0.443	0.4212	0.4562	0.426	0.4468	0.4077	0.4345	0.4033
	HA	Н	В	н	С	H	D
CIE X	CIE Y						
0.4562	0.426	0.4687	0.4289	0.4585	0.4104	0.4468	0.4077
0.4468	0.4077	0.4585	0.4104	0.4483	0.3919	0.4373	0.3893
0.4585	0.4104	0.4703	0.4132	0.4593	0.3944	0.4483	0.3919
0.4687	0.4289	0.481	0.4319	0.4703	0.4132	0.4585	0.4104

## **Mechanical Dimensions**





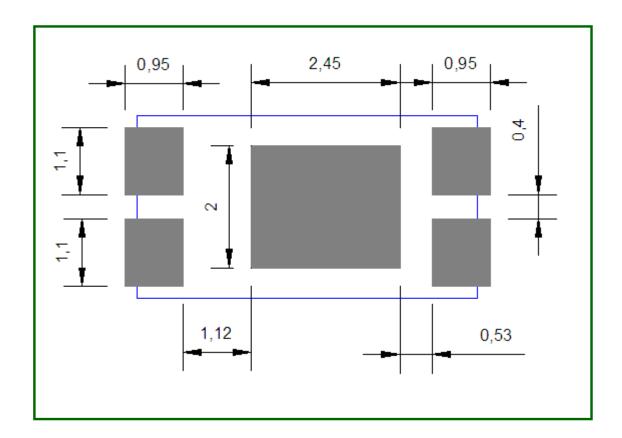
### Notes:

(1) All dimensions are in millimeters.

(2) Scale: none

(3) Undefined tolerance is  $\pm 0.2 mm$ 

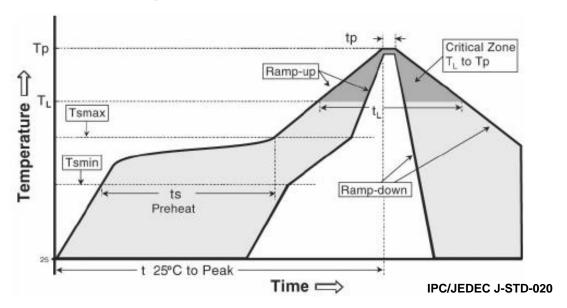
## **Recommended Solder Pad**



### Notes:

- (1) All dimensions are in millimeters.
- (2) Scale: none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is  $\pm 0.1$ mm
- (5) The appearance and specifications of the product may be changed for improvement without notice.

# **Reflow Soldering Characteristics**



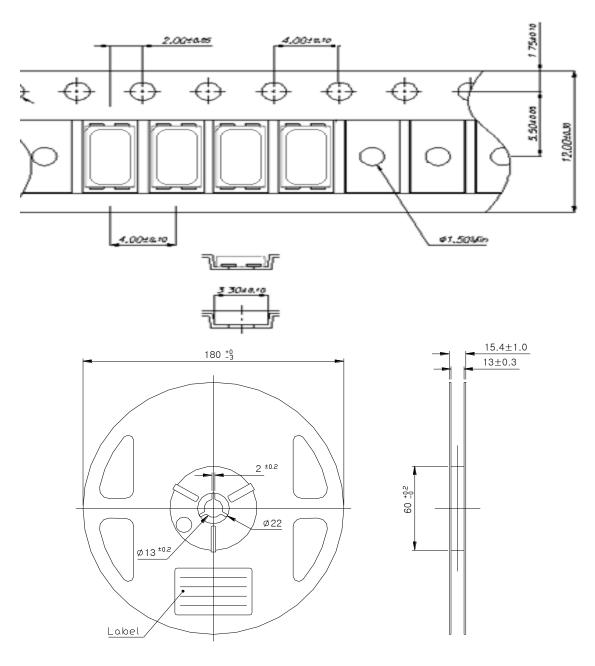
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>s_max</sub> to T <sub>p</sub> )	3° C/second max.	3° C/second max.
$    \begin{array}{c} \textbf{Preheat} \\ \textbf{- Temperature Min } (\textbf{T}_{\textbf{S\_min}}) \\ \textbf{- Temperature Max } (\textbf{T}_{\textbf{S\_max}}) \\ \textbf{- Time } (\textbf{T}_{\textbf{S\_min}} \ \text{to } \textbf{T}_{\textbf{S\_max}}) \ (\textbf{t}_{\textbf{S}}) \\    \end{array} $	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-180 seconds
Time maintained above: - Temperature (T <sub>L</sub> ) - Time (t <sub>L</sub> )	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak Temperature (T <sub>p</sub> )	215℃	260℃
Time within 5°C of actual Peak Temperature (t <sub>p</sub> )2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

### Caution:

- (1) Reflow soldering is recommended not to be done more than two times
  In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered When repair is unavoidable, suitable tools must be used.
- (3) When soldering, do not put stress on the LEDs during heating.
- (4) After soldering, do not warp the circuit board.

Rev0.1, Dec, 2017 17 www.seoulsemicon.com

# **Emitter Tape & Reel Packaging**



( Tolerance:  $\pm 0.2$ , Unit: mm )

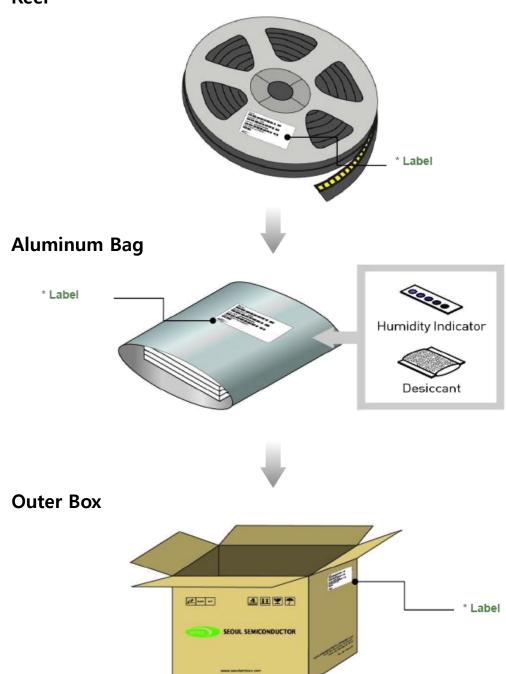
### Notes:

- (1) Quantity: Max 4,500pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be  $\pm 0.2$ mm
- (3) Adhesion Strength of Cover Tape
  Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package: P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.

Rev0.1, Dec, 2017 18 www.seoulsemicon.com

# **Emitter Tape & Reel Packaging**

### Reel



## **Product Nomenclature**

### Table 8. Part Numbering System :

Part Number Code	Description	Part Number	Value
X <sub>1</sub>	Company	S	Seoul Semiconductor
X <sub>2</sub>	Level of Integration	1	Discrete LED
X <sub>3</sub> X <sub>4</sub>	Technology	WO	General White
X <sub>5</sub> X <sub>6</sub> X <sub>7</sub> X <sub>8</sub>	Dimension	5630	
X <sub>9</sub> X <sub>10</sub>	CCT	XX	
X <sub>11</sub> X <sub>12</sub>	CRI	80	
X <sub>13</sub> X <sub>14</sub>	Vf	03	
V V V	Characteristic code	200	
X <sub>15</sub> X <sub>16</sub> X <sub>17</sub>	Flux Rank	000	
X <sub>18</sub> X <sub>19</sub> X <sub>20</sub>	Characteristic code Vf Rank	000	
X <sub>21</sub> X <sub>22</sub>	Characteristic code Color Step	00	
V V	Time	00	
X <sub>23</sub> X <sub>24</sub>	Туре	00	
X <sub>25</sub> X <sub>26</sub> X <sub>27</sub>	Internal code	002	

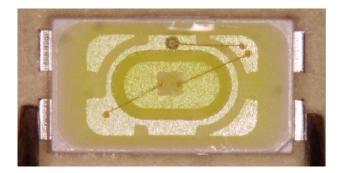


# **Handling of Silicone Resin for LEDs**

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.
- (4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

- (5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

  Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.

Rev0.1, Dec, 2017 21 www.seoulsemicon.com

### **Precaution for Use**

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant.

The recommended storage temperature range is 40°C and a maximum humidity of RH90%.

(2) Use Precaution after Opening the Packaging

Use SMT techniques properly when you solder the LED as separation of the lens may affect the light output efficiency.

Pay attention to the following:

- a. Recommend conditions after opening the package
  - Sealing
  - Temperature : 30°C Humidity : less than RH60%
- b. If the package has been opened more than 4 week(MSL\_2a) or the color of the desiccant changes, components should be dried for 10-24hr at 65±5°C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication. These products are dangerous if they are burned or shredded in the process of disposal. It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

Rev0.1, Dec, 2017 22 www.seoulsemicon.com

### **Precaution for Use**

- (10) The appearance and specifications of the product may be modified for improvement without notice.
- (11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (13) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF.
  If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (15) Similar to most Solid state devices;
  LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
  Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

#### Environmental controls:

- Humidity control (ESD gets worse in a dry environment)



### **Precaution for Use**

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
  (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
  - A surge protection circuit
  - An appropriately rated over voltage protection device
  - A current limiting device



## **Company Information**

#### Published by

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### **Company Information**

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acirch2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

#### **Legal Disclaimer**

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